

N-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A)	Q _g (Typ.)
30	0.023 at V _{GS} = 10 V	8	6.5
	0.025 at V _{GS} = 4.5 V	7.5	
	0.030 at V _{GS} = 3.0 V	6.8	
	0.036 at V _{GS} = 2.5 V	6.0	

FEATURES

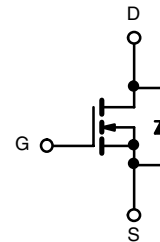
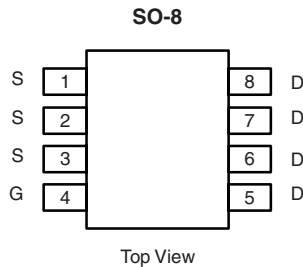
- Halogen-free According to IEC 61249-2-21 Available
- TrenchFET® Gen II Power MOSFET
- 100 % R_g Tested



RoHS
COMPLIANT
HALOGEN
FREE
Available

APPLICATIONS

- High-Side DC/DC Conversion
 - Notebook
 - Desktop
 - Server
- Notebook Logic DC/DC, Low-Side



N-Channel MOSFET

Ordering Information: Si4346DY-T1-E3 (Lead (Pb)-free)
Si4346DY-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted				
Parameter	Symbol	10 s	Steady State	Unit
Drain-Source Voltage	V _{DS}	30		V
Gate-Source Voltage	V _{GS}	± 12		
Continuous Drain Current (T _J = 150 °C) ^a	I _D	T _A = 25 °C	8	5.9
		T _A = 70 °C	6.5	4.7
Pulsed Drain Current	I _{DM}	30		A
Continuous Source Current (Diode Conduction) ^a	I _S	2.2	1.20	
Maximum Power Dissipation ^a	P _D	T _A = 25 °C	2.5	1.31
		T _A = 70 °C	1.6	0.84
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	t ≤ 10 s	R _{thJA}	43	50	°C/W
	Steady State		74	95	
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	22	27	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

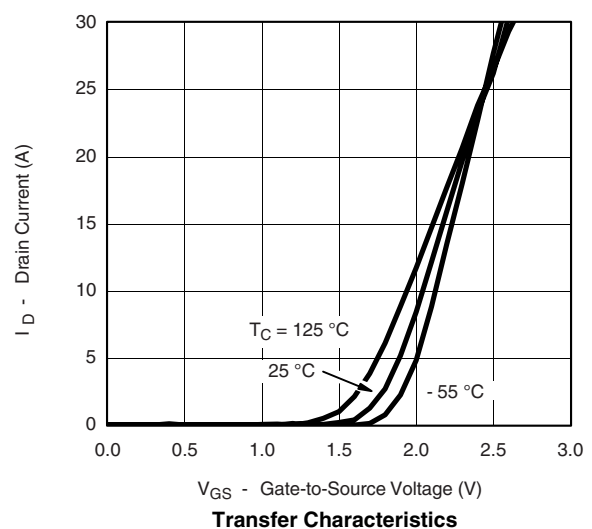
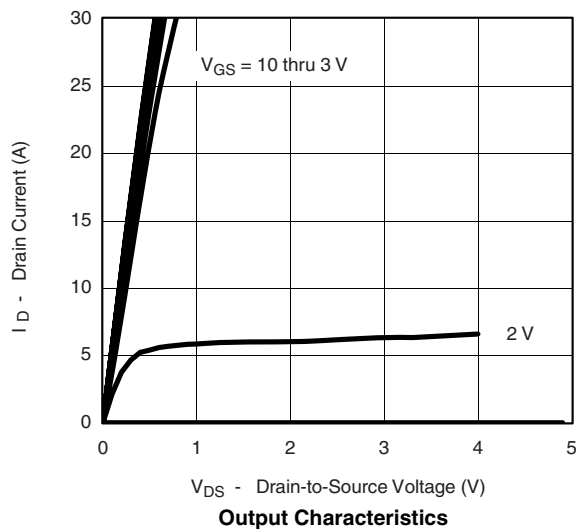
SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	0.7		2.0	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 12\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			5	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	20			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 8\text{ A}$		0.019	0.023	Ω
		$V_{GS} = 4.5\text{ V}, I_D = 7.5\text{ A}$		0.021	0.025	
		$V_{GS} = 3.0\text{ V}, I_D = 6.8\text{ A}$		0.023	0.030	
		$V_{GS} = 2.5\text{ V}, I_D = 6.0\text{ A}$		0.027	0.036	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 8\text{ A}$		32		S
Diode Forward Voltage ^a	V_{SD}	$I_S = 2.2\text{ A}, V_{GS} = 0\text{ V}$		0.75	1.1	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = 15\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 8\text{ A}$		6.5	10	nC
Gate-Source Charge	Q_{gs}			2.3		
Gate-Drain Charge	Q_{gd}			1.1		
Gate Resistance	R_g		0.25	0.5	0.75	Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15\text{ V}, R_L = 15\text{ }\Omega$ $I_D \cong 1\text{ A}, V_{GEN} = 10\text{ V}, R_g = 6\text{ }\Omega$		9	15	ns
Rise Time	t_r			11	17	
Turn-Off Delay Time	$t_{d(off)}$			40	60	
Fall Time	t_f			7	11	
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = 2.2\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}$		20	35	

Notes:

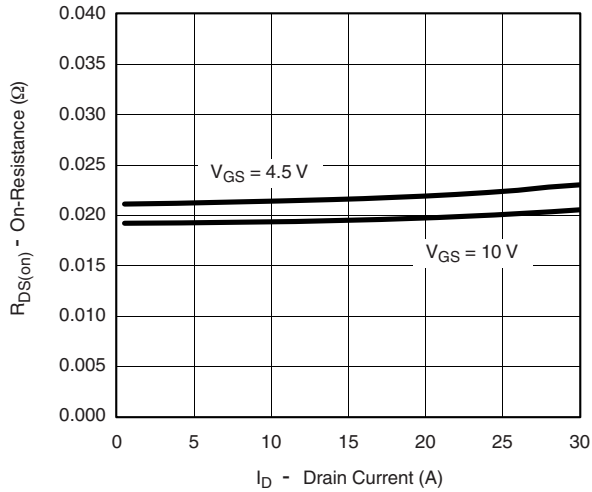
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

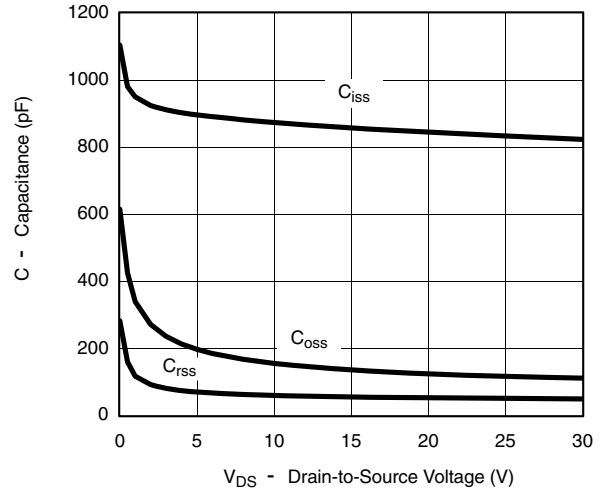
TYPICAL CHARACTERISTICS $25\text{ }^\circ\text{C}$, unless otherwise noted



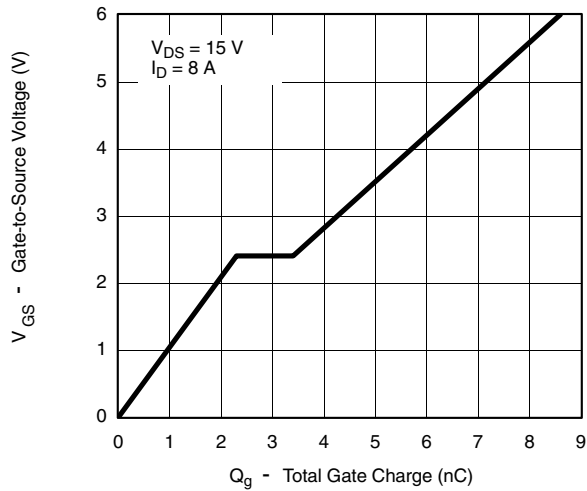
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



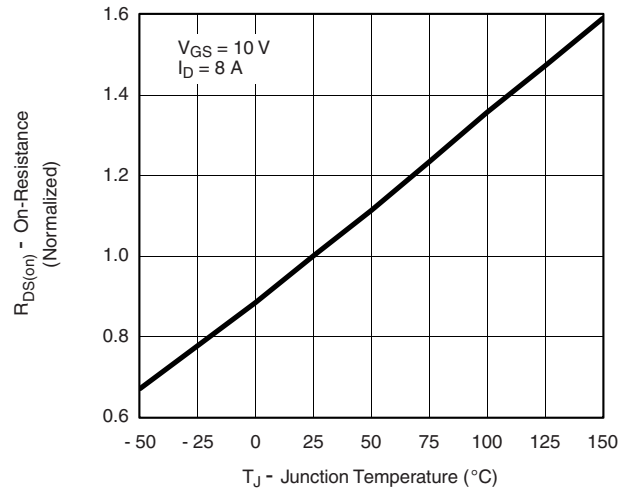
On-Resistance vs. Drain Current



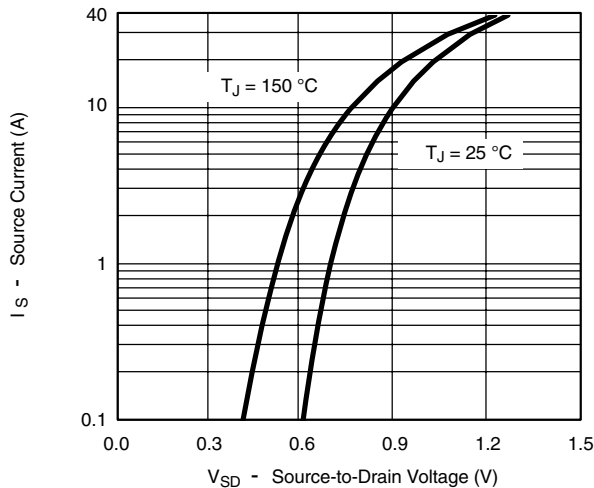
Capacitance



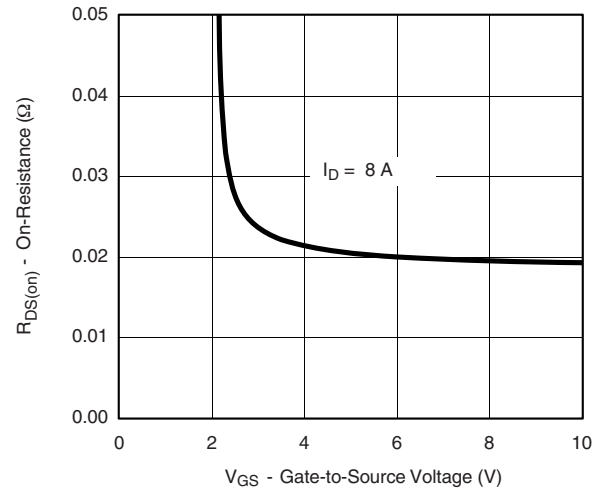
Gate Charge



On-Resistance vs. Junction Temperature

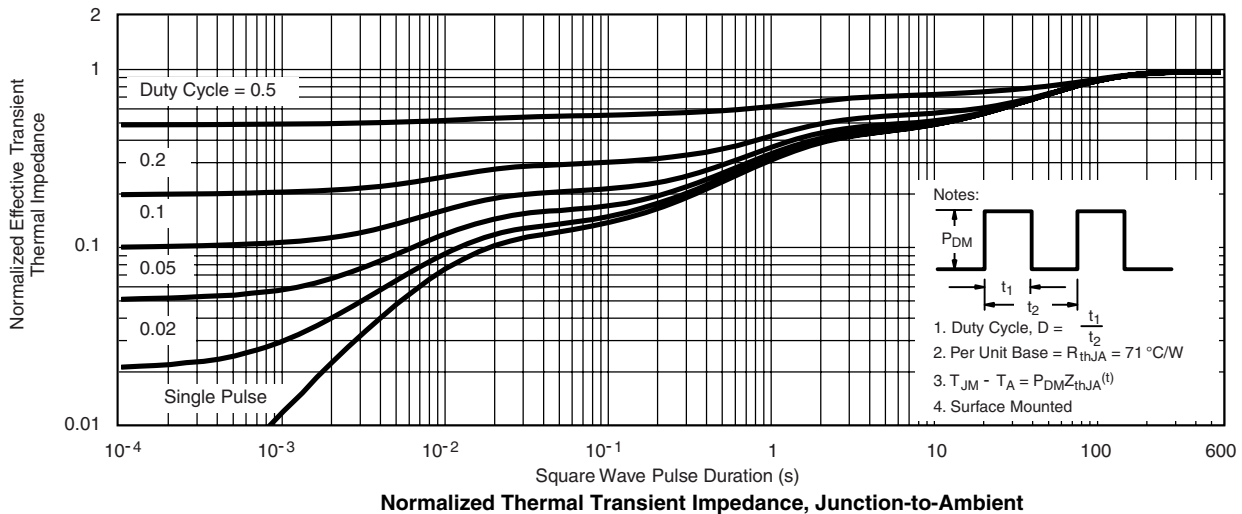
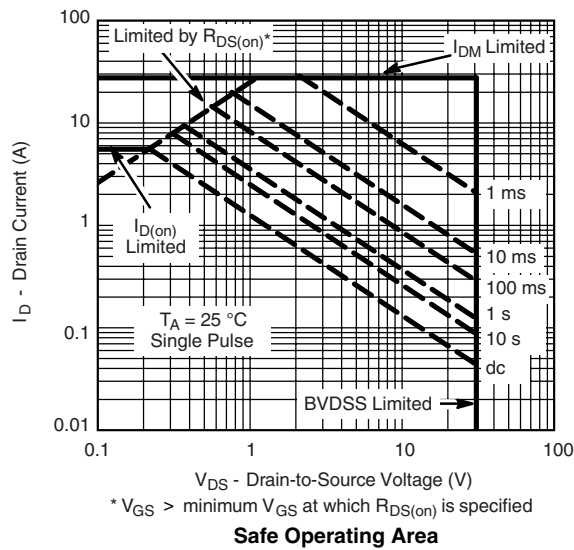
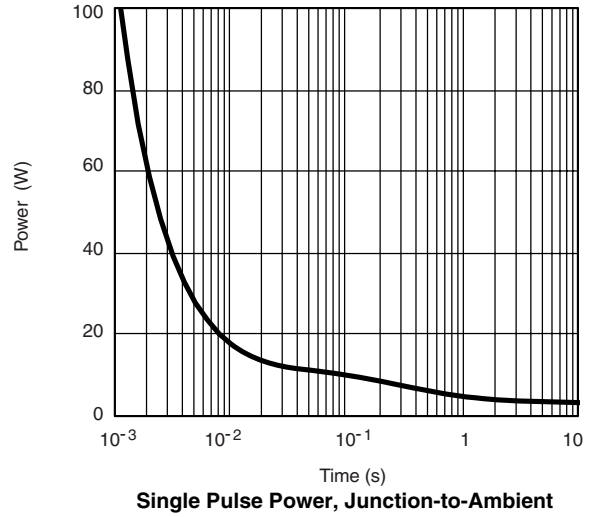
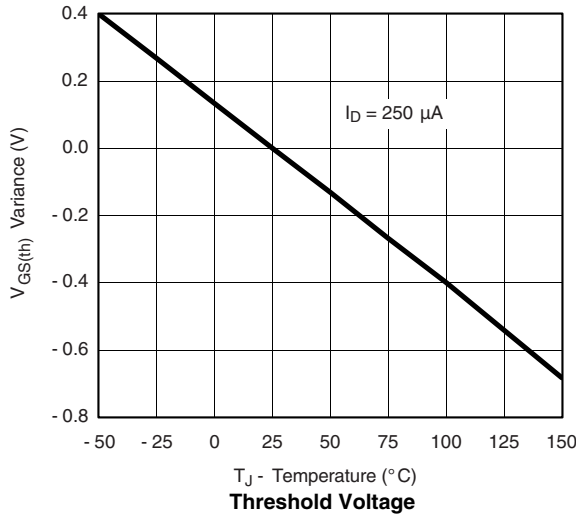


Source-Drain Diode Forward Voltage



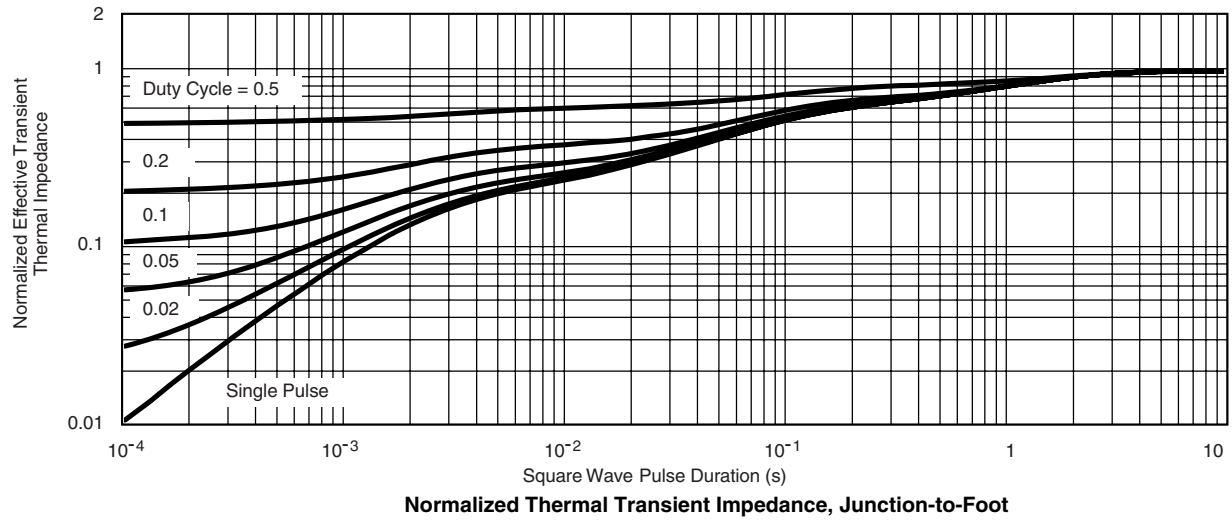
On-Resistance vs. Gate-to-Source Voltage

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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SOIC (NARROW): 8-LEAD

JEDEC Part Number: MS-012



DIM	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A ₁	0.10	0.20	0.004	0.008
B	0.35	0.51	0.014	0.020
C	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°
S	0.44	0.64	0.018	0.026
ECN: C-06527-Rev. I, 11-Sep-06				
DWG: 5498				

RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads
Dimensions in Inches/(mm)

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